



Load Switch with Level-Shift

PRODUCT SUMMARY		
V _{DS2} (V)	r _{DS(on)} (Ω)	I _D (A)
1.8 to 8	0.215 @ V _{IN} = 4.5 V	± 1.2
	0.300 @ V _{IN} = 2.5 V	± 1.0
	0.440 @ V _{IN} = 1.8 V	± 0.7



**ESD Protected
2000 V
1.8-V Rated**

FEATURES

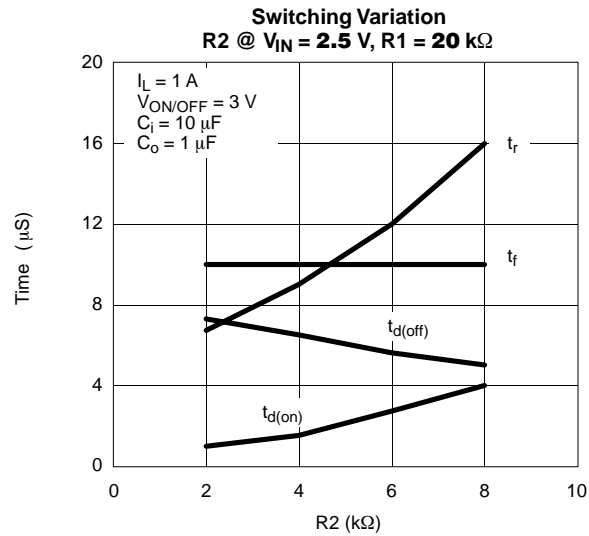
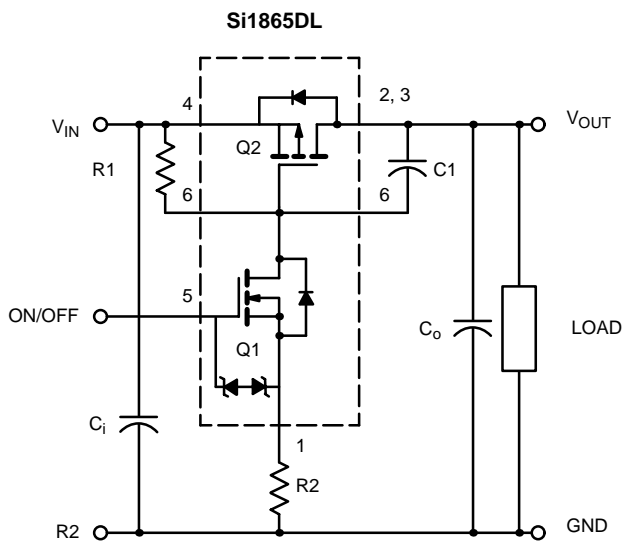
- 215-mΩ Low r_{DS(on)} TrenchFET®
- 1.8 to 8-V Input
- 1.5 to 8-V Logic Level Control
- Low Profile, Small Footprint SC70-6 Package
- 2000-V ESD Protection On Input Switch, V_{ON/OFF}
- Adjustable Slew-Rate

DESCRIPTION

The Si1865DL includes a p- and n-channel MOSFET in a single SC70-6 package. The low on-resistance p-channel TrenchFET is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a level-shift to drive

the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5-V. The Si1865DL operates on supply lines from 1.8 to 8 V, and can drive loads up to 1.2 A.

APPLICATION CIRCUITS

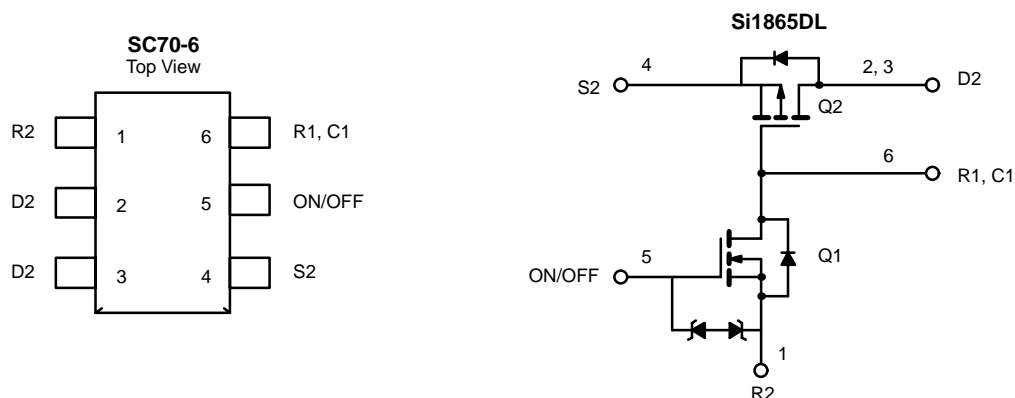


Note: For R2 switching variations with other V_{IN}/R1 combinations See Typical Characteristics

COMPONENTS		
R1	Pull-Up Resistor	Typical 10 kΩ to 1 mΩ*
R2	Optional Slew-Rate Control	Typical 0 to 100 kΩ*
C1	Optional Slew-Rate Control	Typical 1000 pF

*Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

The Si1865DL is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

FUNCTIONAL BLOCK DIAGRAM

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Input Voltage	V _{IN}	8	V
ON/OFF Voltage	V _{ON/OFF}	8	
Load Current	Continuous ^{a, b}	±1.2	A
	Pulsed ^{b, c}	±3	
Continuous Intrinsic Diode Conduction ^a	I _S	-0.4	
Maximum Power Dissipation ^a	P _D	0.4	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)	ESD	2	kV

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (continuous current) ^a	R _{thJA}	260	320	°C/W
Maximum Junction-to-Foot (Q2)	R _{thJC}	180	220	

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

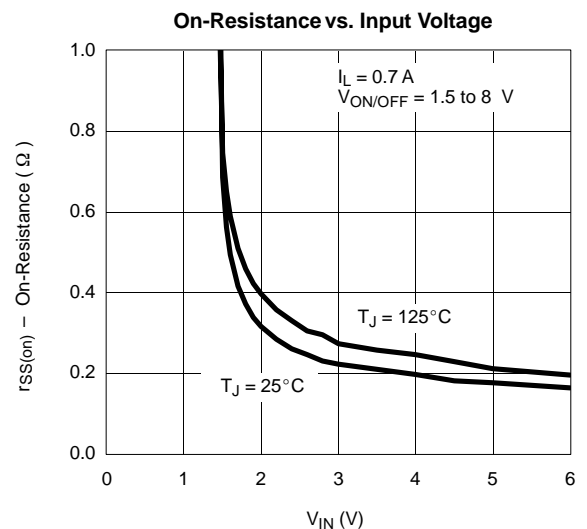
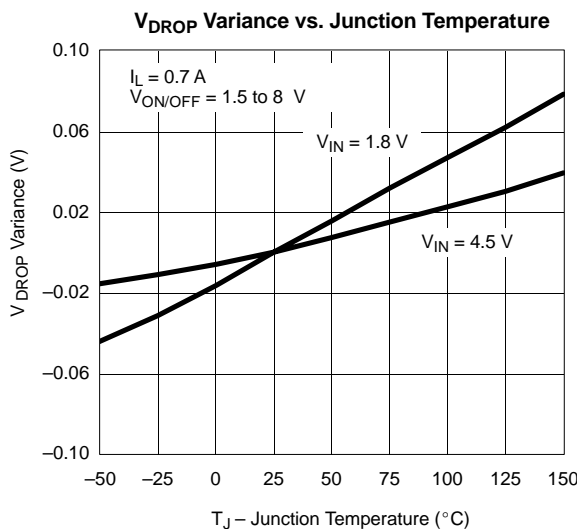
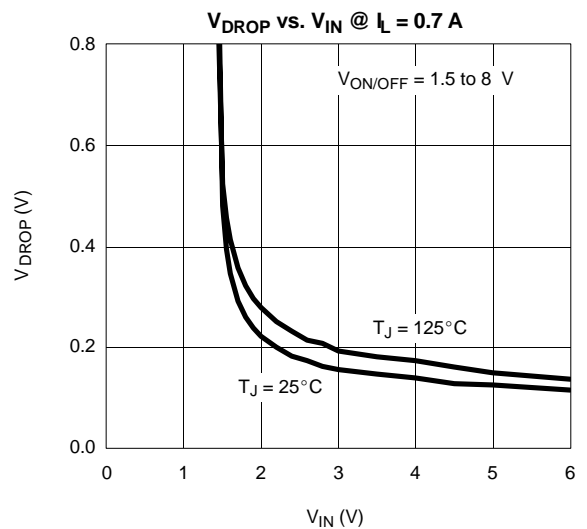
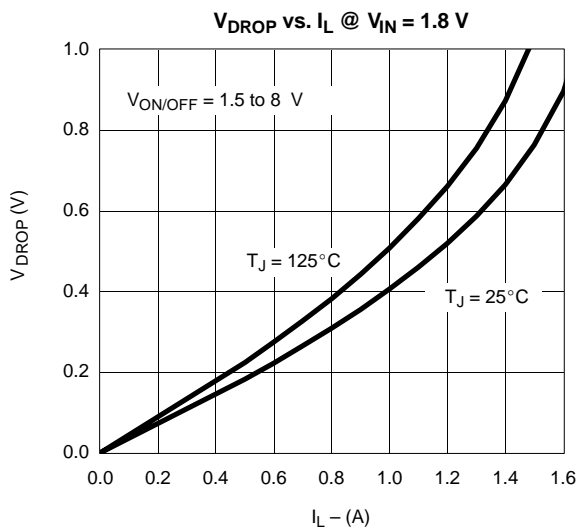
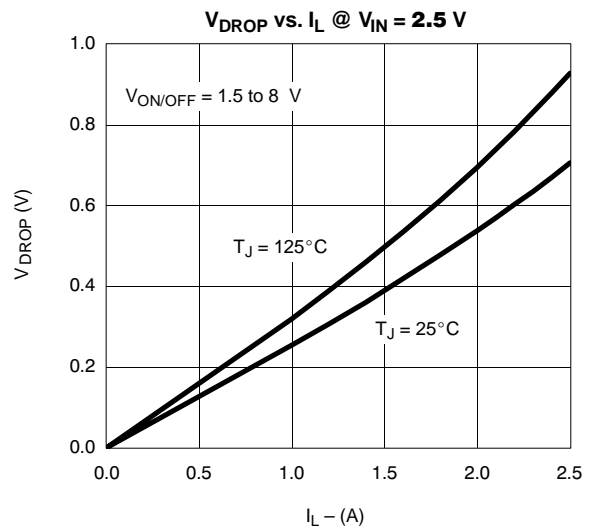
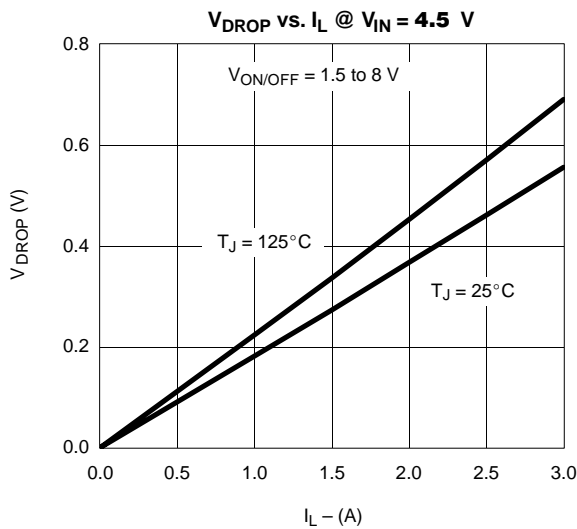
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF Characteristics						
Reverse Leakage Current	I _{FL}	V _{IN} = 8 V, V _{ON/OFF} = 0 V			1	μA
Diode Forward Voltage	V _{SD}	I _S = -0.4 A		0.85	1.1	V
ON Characteristics						
Input Voltage Range	V _{IN}		1.8		8	V
On-Resistance (p-channel) @ 1 A	r _{DS(on)}	V _{ON/OFF} = 1.5 V, V _{IN} = 4.5 V, I _D = 1.2 A		0.180	0.215	Ω
		V _{ON/OFF} = 1.5 V, V _{IN} = 2.5 V, I _D = 1.0 A		0.250	0.300	
		V _{ON/OFF} = 1.5 V, V _{IN} = 1.8 V, I _D = 0.7 A		0.367	0.440	
On-State (p-channel) Drain-Current	I _{D(on)}	V _{IN-OUT} ≤ 0.2 V, V _{IN} = 5 V, V _{ON/OFF} = 1.5 V	1			A
		V _{IN-OUT} ≤ 0.3 V, V _{IN} = 3 V, V _{ON/OFF} = 1.5 V	1			

Notes

- Surface Mounted on FR4 Board.
- V_{IN} = 8 V, V_{ON/OFF} = 8 V, T_A = 25 °C.
- Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

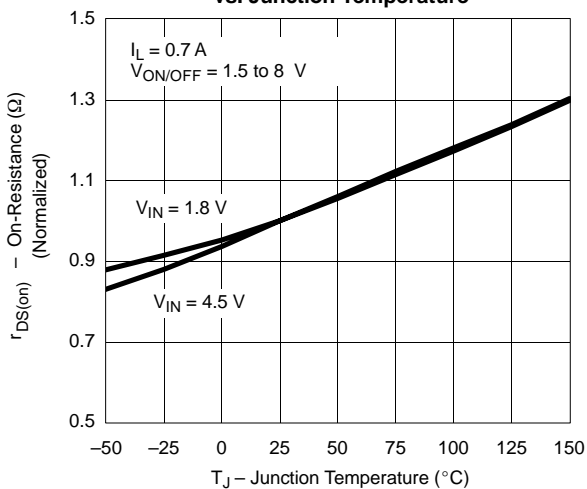


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

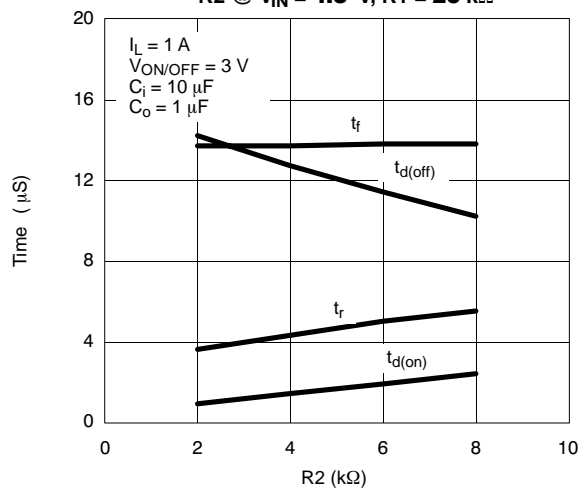


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

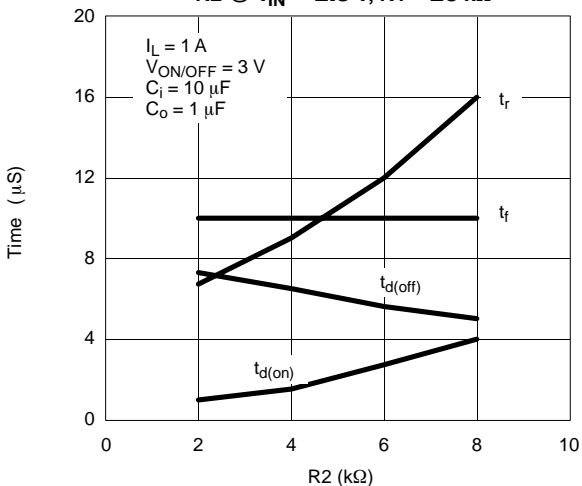
Normalized On-Resistance vs. Junction Temperature



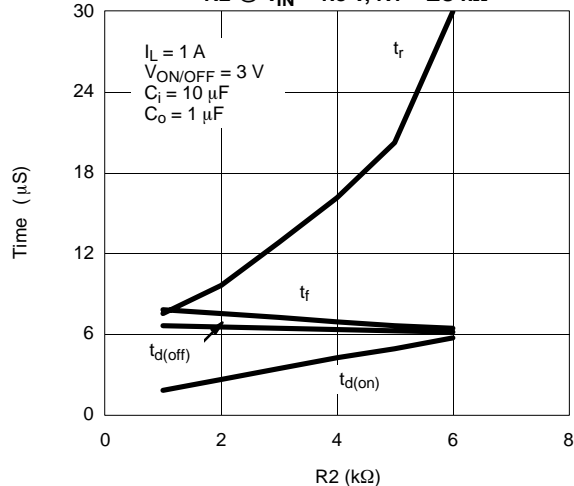
Switching Variation R2 @ V_IN = 4.5 V, R1 = 20 kΩ



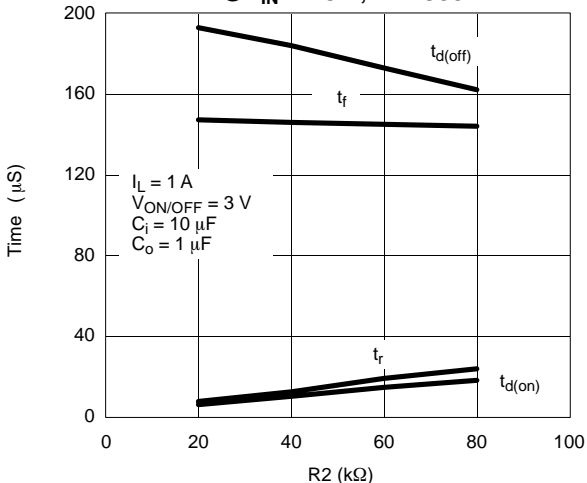
Switching Variation R2 @ V_IN = 2.5 V, R1 = 20 kΩ



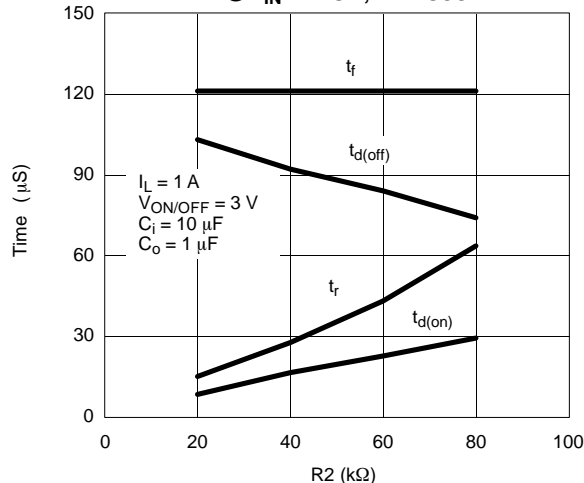
Switching Variation R2 @ V_IN = 1.8 V, R1 = 20 kΩ



Switching Variation R2 @ V_IN = 4.5 V, R1 = 300 kΩ



Switching Variation R2 @ V_IN = 2.5 V, R1 = 300 kΩ



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

